Emanuele Pelucchi

List of Publications by Year
in descending order

206 papers	3,689 citations	136950 32 h-index	168389 53 g-index
208 all docs	208 docs citations	208 times ranked	3380 citing authors

#	Article	IF	Citations
1	The potential and global outlook of integrated photonics for quantum technologies. Nature Reviews Physics, 2022, 4, 194-208.	26.6	151
2	An intuitive protocol for polarization-entanglement restoral of quantum dot photon sources with non-vanishing fine-structure splitting. Scientific Reports, 2022, 12, 4723.	3.3	1
3	Lossless High-speed Silicon Photonic MZI switch with a Micro-Transfer-Printed III-V amplifier. , 2022, , .		0
4	Optical properties and symmetry optimization of spectrally (excitonically) uniform site-controlled GaAs pyramidal quantum dots. Applied Physics Letters, 2021, 118, .	3.3	6
5	Structural and Electronic Properties of Polycrystalline InAs Thin Films Deposited on Silicon Dioxide and Glass at Temperatures below 500 Â°C. Crystals, 2021, 11, 160.	2.2	3
6	Importance of Overcoming MOVPE Surface Evolution Instabilities for >1.3 Î¼m Metamorphic Lasers on GaAs. Crystal Growth and Design, 2021, 21, 2068-2075.	3.0	2
7	Distributing entanglement with separable states: assessment of encoding and decoding imperfections. Quantum Information Processing, 2021, 20, 1.	2.2	0
8	Low Noise Heterogeneous IIIâ€Vâ€onâ€Siliconâ€Nitride Modeâ€Locked Comb Laser. Laser and Photonics Reviews, 2021, 15, 2000485.	8.7	38
9	High Hole Mobility Polycrystalline GaSb Thin Films. Crystals, 2021, 11, 1348.	2.2	3
10	Tertiarybutylarsine damage-free thin-film doping and conformal surface coverage of substrate-released horizontal Si nanowires. Applied Surface Science, 2020, 508, 145147.	6.1	1
11	Edge-Coupling of O-Band InP Etched-Facet Lasers to Polymer Waveguides on SOI by Micro-Transfer-Printing. IEEE Journal of Quantum Electronics, 2020, 56, 1-8.	1.9	8
12	Microtransfer Printing Highâ€Efficiency GaAs Photovoltaic Cells onto Silicon for Wireless Power Applications. Advanced Materials Technologies, 2020, 5, 2000048.	5.8	6
13	Direct visualization of phase-matched efficient second harmonic and broadband sum frequency generation in hybrid plasmonic nanostructures. Light: Science and Applications, 2020, 9, 180.	16.6	24
14	GaAs Photovoltaics: Microtransfer Printing Highâ€Efficiency GaAs Photovoltaic Cells onto Silicon for Wireless Power Applications (Adv. Mater. Technol. 8/2020). Advanced Materials Technologies, 2020, 5, 2070047.	5.8	0
15	Planar Semiconductor Membranes with Brightness Enhanced Embedded Quantum Dots via Electron Beam Induced Deposition of 3D Nanostructures: Implications for Solid State Lighting. ACS Applied Nano Materials, 2020, 3, 12401-12407.	5.0	1
16	Whispering gallery mode emission of low density InP/GaInP quantum dots. AIP Conference Proceedings, 2020, , .	0.4	0
17	Biexciton initialization by two-photon excitation in site-controlled quantum dots: The complexity of the antibinding state case. Applied Physics Letters, 2020, 117, 134001.	3.3	3
18	Microâ€Transferâ€Printed IIIâ€Vâ€onâ€Silicon Câ€Band Semiconductor Optical Amplifiers. Laser and Photonics Reviews, 2020, 14, 1900364.	8.7	50

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19	Next generation low temperature polycrystalline materials for above IC electronics. High mobility n- and p-type IIIâ€“V metalorganic vapour phase epitaxy thin films on amorphous substrates. JPhys Photonics, 2020, 2, 025003.	4.6	4
20	Early stages of InP nanostructure formation on AlInAs. Physical Review B, 2020, 101, .	3.2	4
21	Transfer-print integration of GaAs p-i-n photodiodes onto silicon nitride waveguides for near-infrared applications. Optics Express, 2020, 28, 21275.	3.4	23
22	Micro-transfer-printed III-V-on-silicon C-band distributed feedback lasers. Optics Express, 2020, 28, 32793.	3.4	33
23	Heterogeneous III-V on silicon nitride amplifiers and lasers via microtransfer printing. Optica, 2020, 7, 386.	9.3	84
24	Micro-transfer-printed III-V-on-silicon distributed feedback lasers. , 2020, , .		0
25	Transfer-print integration of GaAs p-i-n photodiodes onto silicon nitride photonic integrated circuits. , 2020, , .		0
26	Exploring conductivity in ex-situ doped Si thin films as thickness approaches 5â€‰nm. Journal of Applied Physics, 2019, 125, 225709.	2.5	12
27	III-V-on-Si photonic integrated circuits realized using micro-transfer-printing. APL Photonics, 2019, 4, .	5.7	108
28	III-V-on-silicon widely tunable laser realized using micro-transfer-printing. , 2019, , .		2
29	Heterogeneous integration in silicon photonics through micro-transfer-printing. , 2019, , .		0
30	Micro-transfer-printing of InP Photonic Devices to Silicon Photonics. , 2019, , .		1
31	Micro-Transfer-Printed III-V-on-Silicon C-Band Distributed Bragg Reflector Laser. , 2019, , .		0
32	Micro-Transfer-Printed III-V-on-Silicon C-Band SOAs with 17 dB Gain. , 2019, , .		1
33	Atomic ordering and bond relaxation in optical spectra of self-organized InP/GaInP2 Wigner molecule structures. Applied Physics Letters, 2019, 115, .	3.3	8
34	On-demand single-photons from electrically-injected site-controlled pyramidal quantum dots. Journal Physics D: Applied Physics, 2019, 52, 045107.	2.8	1
35	Low-power-consumption optical interconnect on silicon by transfer-printing for used in opto-isolators. Journal Physics D: Applied Physics, 2019, 52, 064001.	2.8	5
36	Vanishing biexciton binding energy from stacked, MOVPE grown, site-controlled pyramidal quantum dots for twin photon generation. Journal of Crystal Growth, 2019, 506, 36-39.	1.5	11

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37	Engineering site-controlled quantum dots for optical quantum information processing. , 2019, , .		2
38	Transfer-printing for heterogeneous integration. , 2019, , .		2
39	Three-Dimensional Self-Assembled Columnar Arrays of AlInP Quantum Wires for Polarized Micrometer-Sized Amber Light Emitting Diodes. ACS Photonics, 2018, 5, 1318-1325.	6.6	4
40	Contactless electroreflectance study of the surface potential barrier in <i>n</i>-type and <i>p</i>-type InAlAs van Hoof structures lattice matched to InP. Journal Physics D: Applied Physics, 2018, 51, 215104.	2.8	4
41	Direct or Indirect Bandgap in Hybrid Lead Halide Perovskites?. Advanced Optical Materials, 2018, 6, 1701254.	7.3	54
42	Self-ordered nanostructures on patterned substrates. Journal of Materials Science: Materials in Electronics, 2018, 29, 952-967.	2.2	11
43	Thermal Analysis of InP Lasers Transfer Printed to Silicon Photonics Substrates. Journal of Lightwave Technology, 2018, 36, 5935-5941.	4.6	17
44	Low Threshold Lasing in InP/GaInP Quantum Dot Microdisks. Semiconductors, 2018, 52, 1894-1897.	0.5	3
45	High-Index-Contrast Î» â€‰ =â€‰ 1.55â€‰Î¼m AlInGaAs/InP Laser Heterostructure Waveguides Through Selective Core Oxidation. Physica Status Solidi (A) Applications and Materials Science, 2018, 216, 1800495.	1.8	1
46	AsH3 gas-phase <i>ex situ</i> doping 3D silicon structures. Journal of Applied Physics, 2018, 124, .	2.5	4
47	Transfer-printing-based integration of a III-V-on-silicon distributed feedback laser. Optics Express, 2018, 26, 8821.	3.4	98
48	Pâ€substrate InPâ€based 1.5 Î¼m lasers using an internal carbonâ€doped layer to block pâ€dopant diffusion. Microwave and Optical Technology Letters, 2018, 60, 2363-2367.	1.4	1
49	On-chip optical interconnect on silicon by transfer printing. , 2018, , .		2
50	Excitonic lasing of strain-free InP(As) quantum dots in AlInAs microdisk. Applied Physics Letters, 2017, 110, .	3.3	3
51	Statistical study of stacked/coupled site-controlled pyramidal quantum dots and their excitonic properties. Applied Physics Letters, 2017, 111, .	3.3	6
52	Tuning InP self-assembled quantum structures to telecom wavelength: A versatile original InP(As) nanostructure â€œworkshopâ€. Applied Physics Letters, 2017, 110, 113101.	3.3	6
53	Lasing in microdisks with an active region based on lattice-matched InP/AlInAs nanostructures. Technical Physics, 2017, 62, 1082-1086.	0.7	0
54	Comparison of InGaAs and InAlAs sacrificial layers for release of InP-based devices. Optical Materials Express, 2017, 7, 4408.	3.0	28

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55	Droplet etching of deep nanoholes for filling with self-aligned complex quantum structures. Nanoscale Research Letters, 2016, 11, 282.	5.7	25
56	Monte Carlo simulation of photonic state tomography: a virtual Hanbury Brown and Twiss correlator. European Journal of Physics, 2016, 37, 034002.	0.6	1
57	Lasing of InP/AlInAs quantum dots in AlInAs microdisk cavity. Journal of Physics: Conference Series, 2016, 690, 012023.	0.4	1
58	Lithographically Defined, Room Temperature Low Threshold Subwavelength Red-Emitting Hybrid Plasmonic Lasers. Nano Letters, 2016, 16, 7822-7828.	9.1	23
59	High-efficiency cryogenic temperatures yellow quantum dot for light emitting diodes. , 2016, , .		0
60	Modeling InGaAs MOVPE in V-grooves and pyramidal recesses. , 2016, , .		0
61	Transfer Printing of AlGaInAs/InP Etched Facet Lasers to Si Substrates. IEEE Photonics Journal, 2016, 8, 1-10.	2.0	36
62	Native oxides formation and surface wettability of epitaxial IIIâ€"V materials: The case of InP and GaAs. Applied Surface Science, 2016, 383, 19-27.	6.1	12
63	AlGaAs ridge laser with 33% wall-plug efficiency at 100 Â°C based on a design of experiments approach. Semiconductor Science and Technology, 2016, 31, 045002.	2.0	2
64	Array of entangled-light-emitting diodes with site-controlled pyramidal quantum dots. , 2016, , .		0
65	Selective carrier injection into patterned arrays of pyramidal quantum dots for entangled photon light-emitting diodes. Nature Photonics, 2016, 10, 782-787.	31.4	42
66	Exploring a new transmission window for telecommunications in the 2 Âµm waveband. , 2016, , .		1
67	Shape evolution and emission property of InP nanostructures under hydrides influence. , 2016, , .		0
68	Enabling technologies for a new wavelength window at 2microns. , 2016, , .		0
69	Study of electro-optic effect in asymmetrically ramped AlInGaAs multiple quantum well structures. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 930-935.	1.8	2
70	Unexpected Aspects of Strain Relaxation and Compensation in InGaAs Metamorphic Structures Grown by MOVPE. Crystal Growth and Design, 2016, 16, 2363-2370.	3.0	4
71	40 Gb/s WDM Transmission Over 1.15-km HC-PBGF Using an InP-Based Mach-Zehnder Modulator at 2 Î¼m. Journal of Lightwave Technology, 2016, 34, 1706-1711.	4.6	30
72	Impact of DWDM at 50GHz spacing in the 2Âµm waveband. , 2016, , .		2

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73	A Site-Controlled Quantum Dot Light-Emitting Diode of Polarization-Entangled Photons, Violating Bellâ€™s Inequality. , 2016, , .		0
74	AlInGaAs surface normal photodiode for 2 Âµm optical communication systems. , 2015, , .		8
75	Single pairs of time-bin-entangled photons. Physical Review A, 2015, 92, .	2.5	26
76	Spectral signatures of high-symmetry quantum dots and effects of symmetry breaking. New Journal of Physics, 2015, 17, 103017.	2.9	10
77	Adhesive bonding for mechanically stacked solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 1080-1090.	8.1	28
78	Indium segregation during IIIâ€“V quantum wire and quantum dot formation on patterned substrates. Journal of Applied Physics, 2015, 117, 164313.	2.5	10
79	Semiconductor Quantum Well Lasers With a Temperature-Insensitive Threshold Current. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 177-182.	2.9	4
80	Evaluation of defect density by top-view large scale AFM on metamorphic structures grown by MOVPE. Applied Surface Science, 2015, 349, 849-854.	6.1	5
81	InGaAs Surface Normal Photodiode for 2 <inline-formula> <tex-math notation="LaTeX">$mu ext{m}$ </tex-math></inline-formula> Optical Communication Systems. IEEE Photonics Technology Letters, 2015, 27, 1469-1472.	2.5	15
82	Electrical characterisation of InGaAs on insulator structures. Microelectronic Engineering, 2015, 147, 63-66.	2.4	2
83	10 Gb/s InP-based Mach-Zehnder modulator for operation at 2 Î¼m wavelengths. Optics Express, 2015, 23, 10905.	3.4	13
84	Dense WDM transmission at 2â€‰â€‰Î¼m enabled by an arrayed waveguide grating. Optics Letters, 2015, 40, 3308.	3.3	42
85	Conditions for entangled photon emission from (111)B site-controlled pyramidal quantum dots. Journal of Applied Physics, 2015, 117, .	2.5	31
86	InP-Based Active and Passive Components for Communication Systems at 2 Î¼m. Journal of Lightwave Technology, 2015, 33, 971-975.	4.6	44
87	Complex optical signatures from quantum dot nanostructures and behavior in inverted pyramidal recesses. Physical Review B, 2014, 89, .	3.2	12
88	Unusual nanostructures of â€œlattice matchedâ€•InP on AlInAs. Applied Physics Letters, 2014, 104, 141606.	3.3	7
89	Access resistance reduction in Ge nanowires and substrates based on non-destructive gas-source dopant in-diffusion. Journal of Materials Chemistry C, 2014, 2, 9248-9257.	5.5	18
90	Hot-Electron Injection in Au Nanorodâ€“ZnO Nanowire Hybrid Device for Near-Infrared Photodetection. Nano Letters, 2014, 14, 6202-6209.	9.1	141

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91	Inp-alinas “strain free” early stages heteroepitaxy leading to nanostructure formation by MOVPE. , 2014, , .		0
92	Native oxides formation on MOVPE grown binary III-V materials — Impact on surface wettability. , 2014, , .		0
93	Transient and self-limited nanostructures on patterned surfaces. Physical Review B, 2013, 87, .	3.2	8
94	Evidence of nonadiabatic exciton-phonon interaction probed by second-order LO-phonon replicas of single quantum dots. Physical Review B, 2013, 87, .	3.2	7
95	InAlAs solar cell on a GaAs substrate employing a graded InxGa1â"xAsâ€"InP metamorphic buffer layer. Applied Physics Letters, 2013, 102, .	3.3	23
96	Towards quantum-dot arrays of entangled photon emitters. Nature Photonics, 2013, 7, 527-531.	31.4	185
97	Polarizers in an Asymmetric Twin Waveguide Based on Resonant Coupling. IEEE Photonics Technology Letters, 2013, 25, 1301-1304.	2.5	3
98	Developing an array of site-controlled pyramidal quantum dots emitting polarization-entangled photons. , 2013, , .		0
99	Surfactant role of (TM)Sb in MOVPE growth of metamorphic InGaAs graded buffers. , 2013, , .		0
100	Morphological evolution of seeded self-limiting quantum dots on patterned substrates. , 2013, , .		0
101	Tuning the optical properties of dilute nitride site controlled quantum dots. , 2013, , .		0
102	Microtopography of the eye surface of the crab <i>Carcinus maenas</i> : an atomic force microscope study suggesting a possible antifouling potential. Journal of the Royal Society Interface, 2013, 10, 20130122.	3.4	13
103	Morphological, compositional, and geometrical transients of V-groove quantum wires formed during metalorganic vapor-phase epitaxy. Applied Physics Letters, 2013, 103, .	3.3	5
104	Quantum dot asymmetry and the nature of excited hole states probed by the doubly positively charged exciton<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msup><mml:mi>X</mml:mi><mml:mrow><mml:mn>2</mml:mn><mml:mo>+</mml:mo></mml:mrow></mml:m Physical Review B, 2013, 88, .	3.2	5
105	Chemical and electrical characterization of the HfO2/InAlAs interface. Journal of Applied Physics, 2013, 114, .	2.5	22
106	Site-controlled QDs: A route for dense arrays of integrated entangled photon emitters. , 2013, , .		0
107	Polarization-Entangled Photons from Site-Controlled Pyramidal Quantum Dots. , 2013, , .		0
108	High index contrast optical platform using gallium phosphide on sapphire: an alternative to SOI?. Proceedings of SPIE, 2012, , .	0.8	5

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109	Surface organization of homoepitaxial InP films grown by metalorganic vapor-phase epitaxy. Physical Review B, 2012, 86, .	3.2	24
110	Fine-structure splitting in large-pitch pyramidal quantum dots. Physical Review B, 2012, 85, .	3.2	9
111	SiNx-induced intermixing in AlInGaAs/InP quantum well through interdiffusion of group III atoms. Journal of Applied Physics, 2012, 112, .	2.5	5
112	Compact Electroabsorption Modulators for Photonic Integrated Circuits, Using an Isolated Pedestal Contact Scheme. IEEE Photonics Technology Letters, 2012, 24, 356-358.	2.5	8
113	Quantum well intermixing in AlInGaAs QW structures through the interdiffusion of group III atoms. Proceedings of SPIE, 2012, , .	0.8	0
114	High speed AlInGaAs/InGaAs quantum well waveguide photodiode for wavelengths around 2 microns. , 2012, , .		1
115	Slotted tunable laser with monolithic integrated mode coupler. , 2012, , .		0
116	Sub 10 ps Carrier Response Times in Electroabsorption Modulators Using Quantum Well Offsetting. IEEE Journal of Quantum Electronics, 2012, 48, 1467-1475.	1.9	4
117	Dielectric-Free Fabrication of Compact 30-GHz Photodetectors Using the Isolated Pedestal Contact Configuration. IEEE Photonics Technology Letters, 2012, 24, 1082-1084.	2.5	2
118	Semiconductor nanostructures engineering: Pyramidal quantum dots. Current Opinion in Solid State and Materials Science, 2012, 16, 45-51.	11.5	7
119	Suppression of threading defects formation during Sb-assisted metamorphic buffer growth in InAs/InGaAs/InP structure. Applied Physics Letters, 2012, 100, .	3.3	17
120	On the activation of implanted silicon ions inp-In0.53Ga0.47As. Semiconductor Science and Technology, 2012, 27, 082001.	2.0	6
121	Self-Limiting Evolution of Seeded Quantum Wires and Dots on Patterned Substrates. Physical Review Letters, 2012, 108, 256102.	7.8	35
122	Optical characterization of individual quantum dots. Physica B: Condensed Matter, 2012, 407, 1472-1475.	2.7	3
123	Facetless Tunable Lasers Coupled to Passive Waveguides. , 2012, , .		0
124	Symmetries and the Polarized Optical Spectra of Exciton Complexes in Quantum Dots. Physical Review Letters, 2011, 107, 127403.	7.8	52
125	Optics, morphology, and growth kinetics of GaAs/AlxGa1âˆ’xAs quantum wells grown on vicinal substrates by metalorganic vapor phase epitaxy. Physical Review B, 2011, 84, .	3.2	4
126	Phonon Coupling to Excitonic Transitions in Single InGaAsâˆ•AlGaAs Quantum Dots. AIP Conference Proceedings, 2011, , .	0.4	0

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127	Nitrogen Incorporation Effects On Site-Controlled Quantum Dots. , 2011, , .		1
128	Symmetry Elevation and Symmetry Breaking: Keys to Describe and Explain Excitonic Complexes in Semiconductor Quantum Dots. AIP Conference Proceedings, 2011, , .	0.4	0
129	Active semiconductor nanophotonics based on deterministic quantum wire and dot systems. Proceedings of SPIE, 2011, , .	0.8	0
130	A study of nitrogen incorporation in pyramidal site-controlled quantum dots. Nanoscale Research Letters, 2011, 6, 567.	5.7	8
131	Remote phonon and surface roughness limited universal electron mobility of In0.53Ga0.47As surface channel MOSFETs. Microelectronic Engineering, 2011, 88, 1083-1086.	2.4	27
132	Relevance of the purity level in a MetalOrganic Vapour Phase Epitaxy reactor environment for the growth of high quality pyramidal site-controlled Quantum Dots. Journal of Crystal Growth, 2011, 315, 119-122.	1.5	7
133	Physical properties of highly uniform InGaAs pyramidal quantum dots with GaAs barriers: Fine structure splitting in pre-patterned substrates. Superlattices and Microstructures, 2011, 49, 279-282.	3.1	3
134	Decomposition, diffusion, and growth rate anisotropies in self-limited profiles during metalorganic vapor-phase epitaxy of seeded nanostructures. Physical Review B, 2011, 83, .	3.2	36
135	On the calculation of effective electric field in In0.53Ga0.47As surface channel metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2011, 98, 193501.	3.3	5
136	Exciton-phonon coupling in single quantum dots with different barriers. Applied Physics Letters, 2011, 98, .	3.3	6
137	Wettability and â€œpetal effectâ€• of GaAs native oxides. Journal of Applied Physics, 2011, 110, .	2.5	9
138	Low-angle misorientation dependence of the optical properties of InGaAs/InAlAs quantum wells. Journal of Crystal Growth, 2010, 312, 1546-1550.	1.5	13
139	AlGaAs/GaAs/AlGaAs quantum wells as a sensitive tool for the MOVPE reactor environment. Journal of Crystal Growth, 2010, 312, 3057-3062.	1.5	38
140	Pyramidal quantum dots: High uniformity and narrow excitonic emission. Superlattices and Microstructures, 2010, 47, 78-82.	3.1	4
141	Physics of novel site controlled InGaAs quantum dots on (111) oriented substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2761-2764.	2.7	11
142	Growth and structural characterization of pyramidal siteâ€controlled quantum dots with high uniformity and spectral purity. Physica Status Solidi (B): Basic Research, 2010, 247, 1862-1866.	1.5	16
143	Crystal defect topography of Stranskiâ€"Krastanow quantum dots by atomic force microscopy. Applied Physics Letters, 2010, 97, .	3.3	8
144	Impact of nitrogen incorporation on pseudomorphic site-controlled quantum dots grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 97, .	3.3	10

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145	Phonon replicas of charged and neutral exciton complexes in single quantum dots. Physical Review B, 2010, 82, .	3.2	7
146	Fine structure of exciton complexes in high-symmetry quantum dots: Effects of symmetry breaking and symmetry elevation. Physical Review B, 2010, 81, .	3.2	86
147	Pyramidal<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaAs</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Al</mml:m wire/dot systems with controlled heterostructure potential. Physical Review B, 2010, 82, .	3.2	17
148	Design of single growth epitaxial structures for monolithic integration of single frequency laser and Electro-absorption modulators. , 2009, , .		1
149	A site-controlled quantum dot system offering both high uniformity and spectral purity. Applied Physics Letters, 2009, 94, 223121.	3.3	78
150	Hybridization of Electron and Hole States in Semiconductor Quantumâ€Dot Molecules. Small, 2009, 5, 329-335.	10.0	16
151	Coulomb correlations of charged excitons in semiconductor quantum dots. Physical Review B, 2009, 80, .	3.2	18
152	Valence Band Engineering and Polarization Switching in Quantum Dots grown in Inverted Pyramids. , 2009, , .		0
153	Magneto-photoluminescence of heavy- and light-hole excitons in site-controlled pyramidal quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1873-1875.	2.7	1
154	Quantum dot molecules realized with modulated quantum wire heterostructrues. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1815-1818.	2.7	6
155	Theory and experiment of step bunching on misoriented GaAs(001) during metalorganic vapor-phase epitaxy. Applied Physics Letters, 2008, 92, 013117.	3.3	31
156	Control of valence band states in pyramidal quantum dot-in-dot semiconductor heterostructures. Applied Physics Letters, 2007, 91, .	3.3	16
157	Excited excitonic states observed in semiconductor quantum dots using polarization resolved optical spectroscopy. Journal of Applied Physics, 2007, 101, 081703.	2.5	20
158	Narrow (â‰ˆ4meV) inhomogeneous broadening and its correlation with confinement potential of pyramidal quantum dot arrays. Applied Physics Letters, 2007, 91, 081106.	3.3	29
159	Transition from Two-Dimensional to Three-Dimensional Quantum Confinement in Semiconductor Quantum Wires/Quantum Dots. Nano Letters, 2007, 7, 2227-2233.	9.1	46
160	Mechanisms of Quantum Dot Energy Engineering by Metalorganic Vapor Phase Epitaxy on Patterned Nonplanar Substrates. Nano Letters, 2007, 7, 1282-1285.	9.1	51
161	Step ordering induced by nonplanar patterning of GaAs surfaces. Applied Physics Letters, 2006, 88, 203104.	3.3	6
162	Correlation between optical properties and interface morphology of GaAsâˆ•AlGaAs quantum wells. Applied Physics Letters, 2006, 88, 141917.	3.3	15

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163	Luttinger-Liquid Behavior in Weakly Disordered Quantum Wires. Physical Review Letters, 2006, 97, 196802.	7.8	48
164	Alloy Segregation, Quantum Confinement, and Carrier Capture in Self-Ordered Pyramidal Quantum Wires. Nano Letters, 2006, 6, 1036-1041.	9.1	39
165	Time-resolved cathodoluminescence of InGaAs/AlGaAs tetrahedral pyramidal quantum structures. Applied Physics B: Lasers and Optics, 2006, 84, 343-350.	2.2	17
166	Controlling interface reactivity and Schottky barrier height in Auâ^•ZnSe(001) junctions. Journal of Vacuum Science & Technology B, 2006, 24, 1259.	1.3	3
167	Optical polarization anisotropy and hole states in pyramidal quantum dots. Applied Physics Letters, 2006, 89, 251113.	3.3	44
168	Sub-meV photoluminescence linewidth and >106cm2â^•Vs electron mobility in AlGaAsâ^•GaAs quantum wells grown by metalorganic vapor phase epitaxy on slightly misoriented substrates. Journal of Applied Physics, 2006, 99, 093515.	2.5	30
169	Optimization of the efficiency of single-photon sources based on quantum dots under optical excitation. Applied Physics Letters, 2006, 88, 081905.	3.3	15
170	Quantum-dot exciton dynamics probed by photon-correlation spectroscopy. Physical Review B, 2006, 73, .	3.2	55
171	Influence of long-range substrate roughness on disorder in V-groove quantum wire structures. Journal of Applied Physics, 2006, 100, 123509.	2.5	2
172	Correlated photon emission from semiconductor quantum dots grown in inverted pyramids. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 194-198.	2.7	4
173	Enhancement of the binding energy of charged excitons in disordered quantum wires. Physical Review B, 2005, 71, .	3.2	21
174	Probing carrier dynamics in nanostructures by picosecond cathodoluminescence. Nature, 2005, 438, 479-482.	27.8	157
175	Epitaxial Al/GaN and Au/GaN junctions on as-grown GaN(0001)1 Ã— 1 surfaces. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 804-807.	1.8	1
176	Charged excitons in modulation-doped quantum wires. AIP Conference Proceedings, 2005, , .	0.4	0
177	Single-photon emission from pyramidal quantum dots: The impact of hole thermalization on photon emission statistics. Physical Review B, 2005, 72, .	3.2	31
178	Growth and characterization of single quantum dots emitting at 1300 nm. Applied Physics Letters, 2005, 86, 101908.	3.3	153
179	Patterning of confined-state energies in site-controlled semiconductor quantum dots. Applied Physics Letters, 2005, 86, 243105.	3.3	11
180	Single photon emission from site-controlled pyramidal quantum dots. Applied Physics Letters, 2004, 84, 648-650.	3.3	110

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181	Localization of excitons in disordered quantum wires probed by single-photon correlation spectroscopy. Applied Physics Letters, 2004, 85, 5715-5717.	3.3	8
182	Electroluminescence from a single pyramidal quantum dot in a light-emitting diode. Applied Physics Letters, 2004, 84, 1967-1969.	3.3	32
183	Local interface composition and native stacking fault density in ZnSeâˆ•GaAs(001) heterostructures. Journal of Applied Physics, 2004, 96, 2592-2602.	2.5	21
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